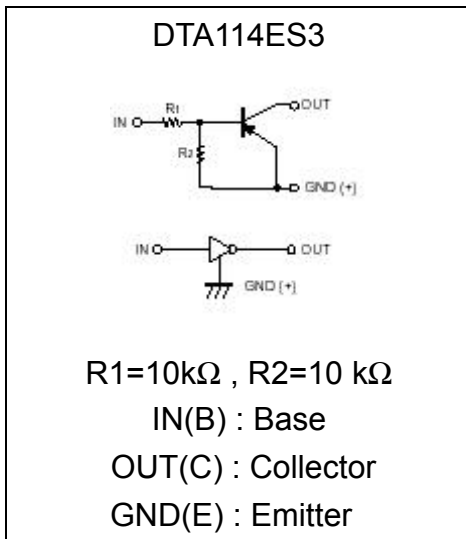
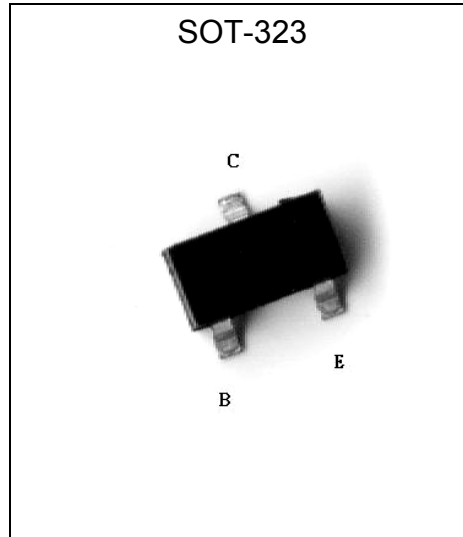


PNP Digital Transistors (Built-in Resistors)

DTA114ES3

Features

- Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
- The bias resistors consist of thin-film resistors with complete isolation to allow positive biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
- Only the on/off conditions need to be set for operation, making device design easy.
- Complements the DTC114ES3

Equivalent Circuit

Outline

Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Supply Voltage	V _{CC}	-50	V
Input Voltage	V _{IN}	-40~+10	V
Output Current	I _O	-50	mA
	I _{O(max)}	-100	mA
Power Dissipation	P _d	200	mW
Thermal Resistance, Junction to Ambient	R _{θJA}	625	°C/W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55~+150	°C



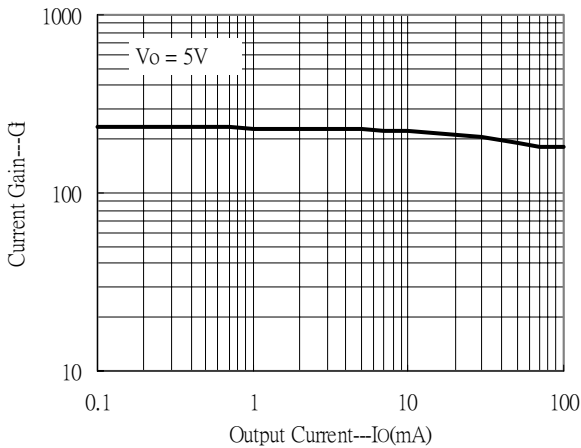
Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Input Voltage	$V_{I(off)}$	-	-	-0.5	V	$V_{CC}=-5V, I_o=-100\mu A$
	$V_{I(on)}$	-3	-	-	V	$V_o=-0.3V, I_o=-10mA$
Output Voltage	$V_{O(on)}$	-	-	-0.3	V	$I_o/I_i=-10mA/-0.5mA$
Input Current	I_i	-	-	-0.88	mA	$V_i=-5V$
Output Current	$I_{O(off)}$	-	-	-0.5	μA	$V_{CC}=-50V, V_i=0V$
DC Current Gain	G_i	30	-	-	-	$V_o=-5V, I_o=-5mA$
Input Resistance	R_i	7	10	13	$k\Omega$	-
Resistance Ratio	R_2/R_1	0.8	1	1.2	-	-
Transition Frequency	f_T	-	250	-	MHz	$V_{CE}=-10V, I_c=-5mA, f=100MHz$ *

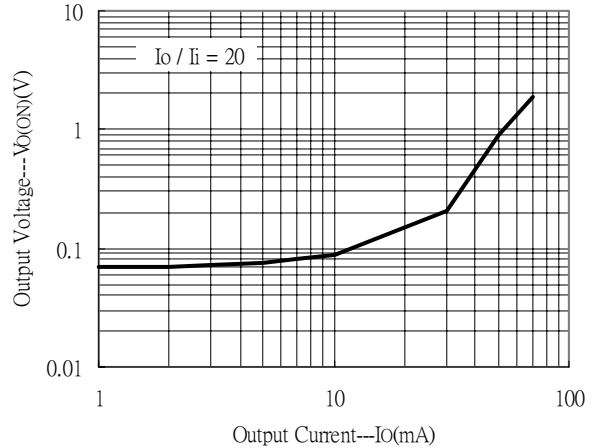
* Transition frequency of the device

Characteristic Curves

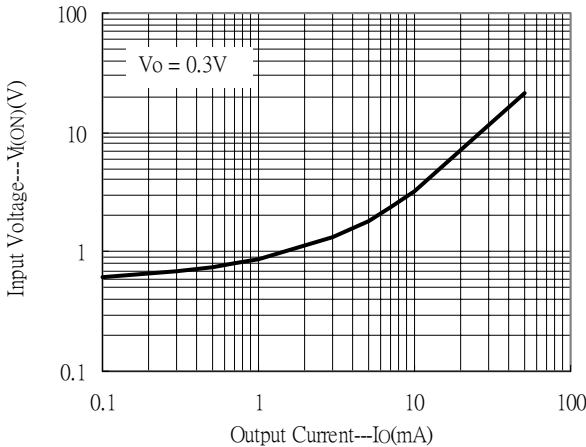
Current Gain vs Output Current



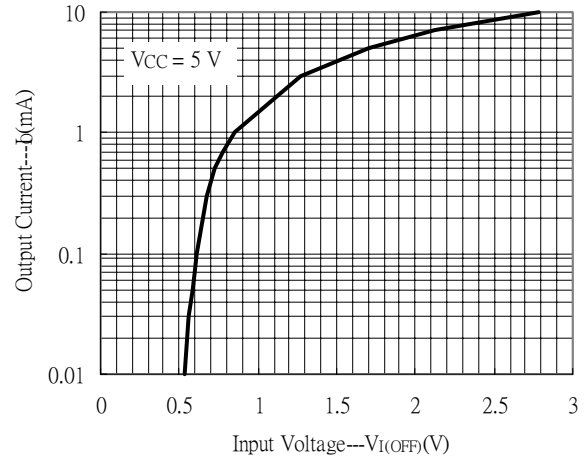
Output Voltage vs Output Current



Input Voltage vs Output Current(ON characteristics)

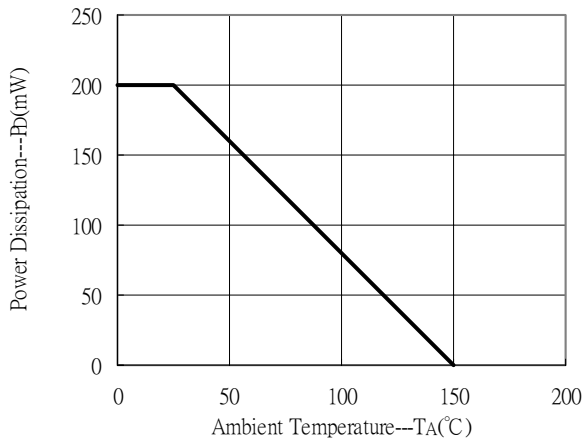


Output Current vs Input Voltage(OFF characteristics)

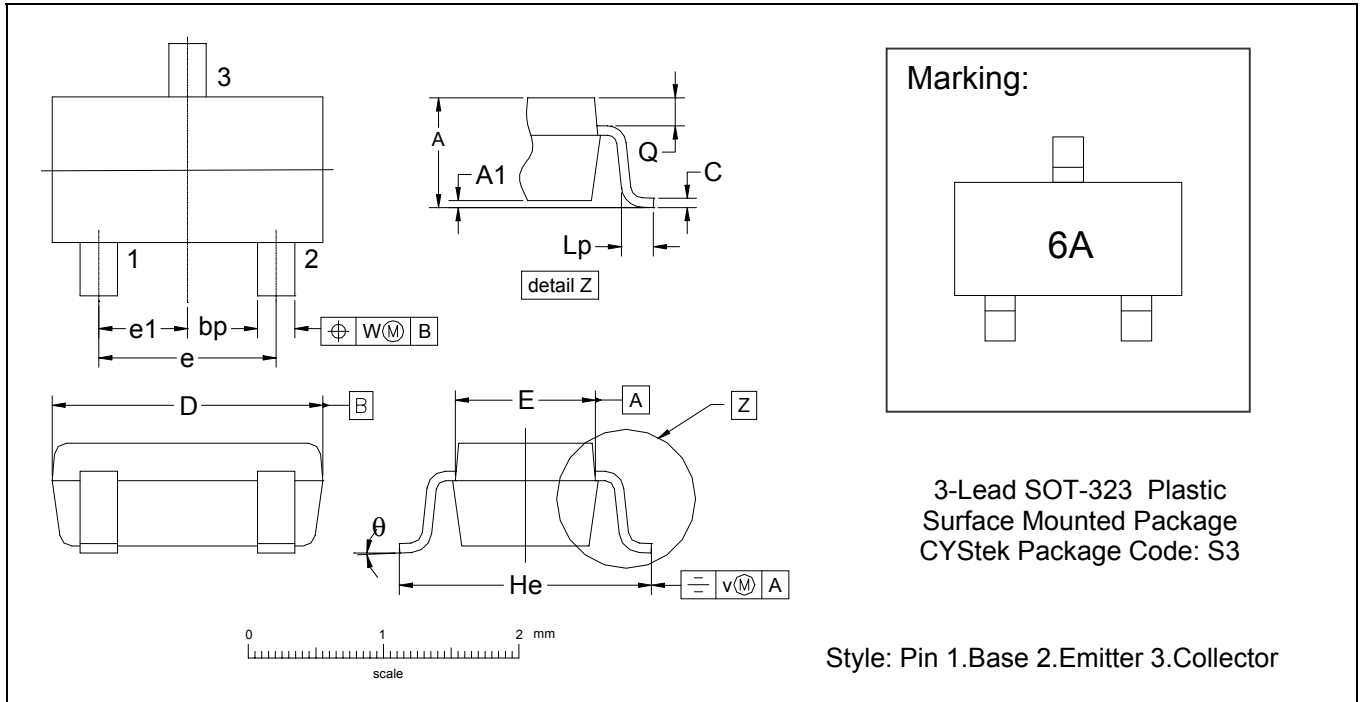




Power Derating Curve



SOT-323 Dimension



*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.0315	0.0433	0.80	1.10	e1	0.0256	-	0.65	-
A1	0.0000	0.0039	0.00	0.10	He	0.0787	0.0886	2.00	2.25
bp	0.0118	0.0157	0.30	0.40	Lp	0.0059	0.0177	0.15	0.45
C	0.0039	0.0098	0.10	0.25	Q	0.0051	0.0091	0.13	0.23
D	0.0709	0.0866	1.80	2.20	v	0.0079	-	0.2	-
E	0.0453	0.0531	1.15	1.35	w	0.0079	-	0.2	-
e	0.0512	-	1.3	-	θ	-	-	10°	0°

Notes: 1.Controlling dimension: millimeters.
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: 42 Alloy ; solder plating
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

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